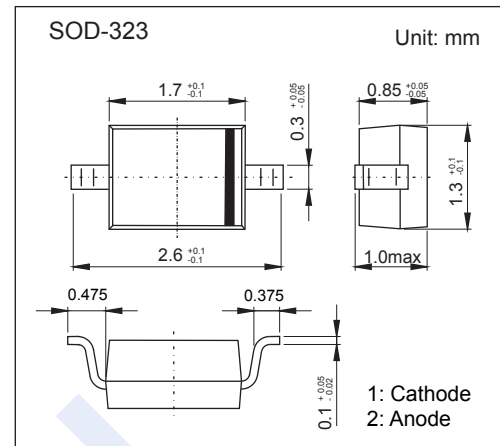


Switching Diodes

DA2J101

■ Features

- Small reverse current I_R
- Short reverse recovery time t_{rr}
- Contributes to miniaturization of sets, reduction of component count.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_R	80	V
Maximum Peak Reverse Voltage	V_{RM}	80	
Forward Current	I_F	100	mA
Peak Forward Surge Current	I_{FM}	225	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	500	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100\text{ }\mu\text{A}$	80			V
Forward voltage	V_F	$I_F = 100\text{ mA}$			1.2	
Reverse voltage leakage current	I_R	$V_R = 80\text{ V}$			100	nA
Junction capacitance	C_j	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$			1.2	pF
Reverse recovery time	t_{rr}	$I_F = 10\text{ mA}$, $I_{rr} = 0.1 I_R$, $V_R = 6\text{ V}$			3	ns

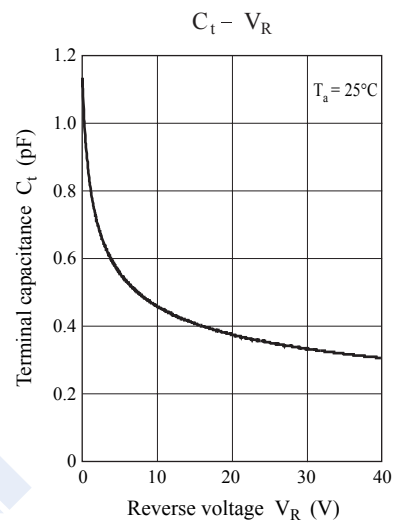
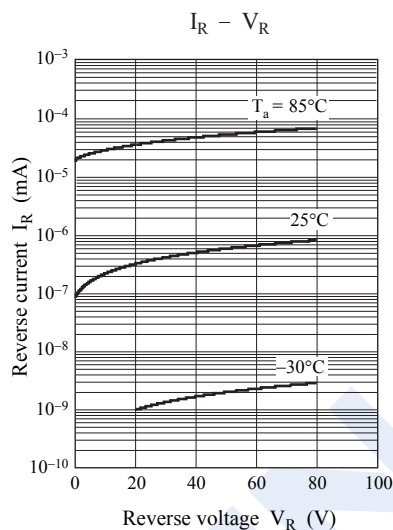
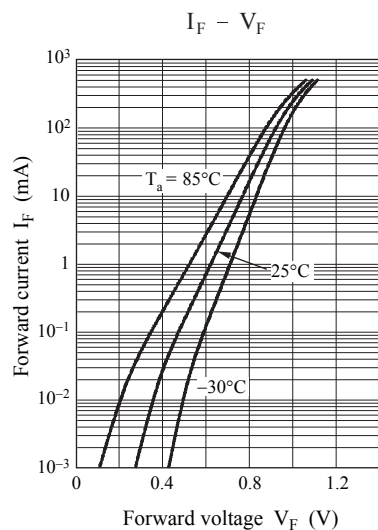
■ Marking

Marking	A1
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Switching Diodes

DA2J101

■ Typical Characteristics

 t_{rr} measurement circuit